



#### 30V N-CHANNEL ENHANCEMENT MODE MOSFET

#### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C		
30V	$21m\Omega$ @ $V_{GS} = 10V$	8.5A		
	$35m\Omega @ V_{GS} = 4.5V$	6.6A		

#### **Description**

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP.

### **Applications**

- Backlighting
- Power Management Functions
- DC-DC Converters

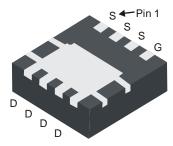
### **Features and Benefits**

- Low R<sub>DS(ON)</sub> ensures on state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

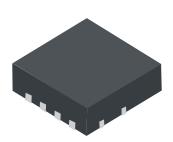
#### **Mechanical Data**

- Case: POWERDI<sup>®</sup>3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe Solderable per MIL-STD-202, Method 208 ©3
- Weight: 0.072 grams (Approximate)

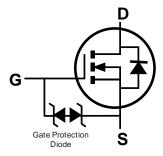








Top View



Top View Internal Schematic

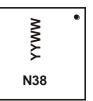
### **Ordering Information** (Note 5)

Part Number	Case	Packaging
DMN3018SFGQ-7	POWERDI®3333-8	2000/Tape & Reel
DMN3018SFGQ-13	POWERDI®3333-8	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product\_compliance\_definitions.html.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



N38 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 11 = 2011) WW = Week Code (01 to 53)



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Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			V <sub>DSS</sub>	30	V
Gate-Source Voltage			V <sub>GSS</sub>	±25	V
Ocationary Davis Comment (Note 7) V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	8.5 6.8	А
Continuous Drain Current (Note 7) V <sub>GS</sub> = 10V	t<10s	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	11.3 9.1	Α
Continuous Prain Current (Note 7) // 45/	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	6.6 5.3	А
Continuous Drain Current (Note 7) V <sub>GS</sub> = 4.5V	t<10s	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	8.7 7.0	А
Maximum Continuous Body Diode Forward Current (Note 7)			I <sub>S</sub>	2.5	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	60	Α
Avalanche Current (Note 8) L = 0.1mH			I <sub>AS</sub>	18	Α
Avalanche Energy (Note 8) L = 0.1mH			Eas	16	mJ

### **Thermal Characteristics**

Characteristic		Symbol	Value	Unit	
Total Power Dissipation (Note 6)		$P_{D}$	1.0	W	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	126	°C/W	
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{\theta JA}$	71		
Total Power Dissipation (Note 7)		$P_{D}$	2.2	W	
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	6	56	°C/W	
Themal Resistance, Junction to Ambient (Note 1)	t<10s	$R_{\theta JA}$	31		
Thermal Resistance, Junction to Case		$R_{\theta JC}$	7.0		
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C	

## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)						•	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 24V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)	-			•			
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	1.7	2.1	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance		_	16	21	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 10A	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	21	35	11122	$V_{GS} = 4.5V, I_D = 8.5A$	
Diode Forward Voltage	$V_{SD}$	0.5	_	1.2	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C <sub>iss</sub>	_	697	_	pF	45)/ )/ 6)/	
Output Capacitance	Coss	_	97	_	pF	$V_{DS} = 15V, V_{GS} = 0V,$ - f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	67	_	pF	1 = 1.0Winz	
Gate Resistance	R <sub>g</sub>	_	1.47	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	_	6.0	_	nC		
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	13.2	_	nC	$V_{GS} = 10V, V_{DS} = 15V,$	
Gate-Source Charge	Qgs	_	2.2	_	nC	I <sub>D</sub> = 9A	
Gate-Drain Charge	Q <sub>gd</sub>	_	1.8	_	nC	1	
Turn-On Delay Time	t <sub>D(ON)</sub>	_	4.3	_	ns		
Turn-On Rise Time	t <sub>R</sub>	_	4.4	_	ns	V <sub>DD</sub> = 15V, V <sub>GS</sub> = 10V,	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	20.1	_	ns	$R_L = 15\Omega$ , $I_D = 1A$ , $R_G = 6\Omega$	
Turn-Off Fall Time	t <sub>F</sub>	_	4.1	_	ns	1	
Reverse Recovery Time	t <sub>RR</sub>	_	7.3	_	ns		
Reverse Recovery Charge	Q <sub>RR</sub>	_	7.9	_	nC	$I_F = 9A$ , di/dt = $500A/\mu s$	

Notes: 6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

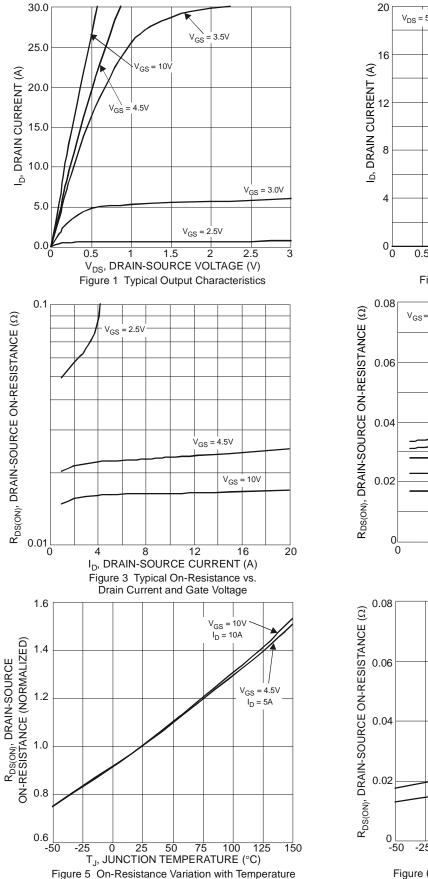
7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

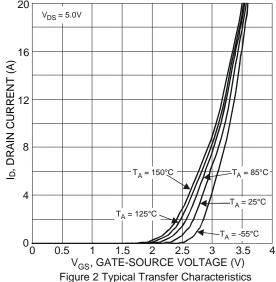
8.  $I_{AS}$  and  $E_{AS}$  ratings are based on low frequency and duty cycles to keep  $T_J$  = +25°C.

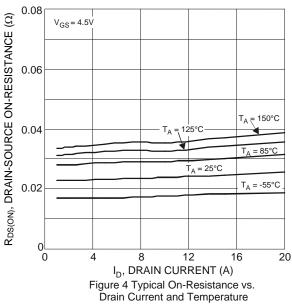
9. Short duration pulse test used to minimize self-heating effect.

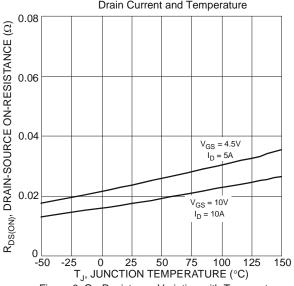
10. Guaranteed by design. Not subject to product testing.















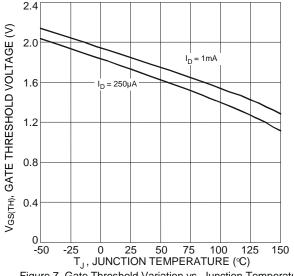
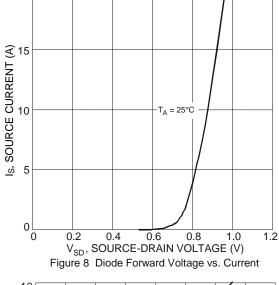
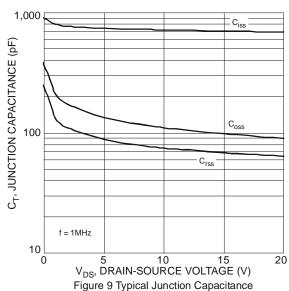


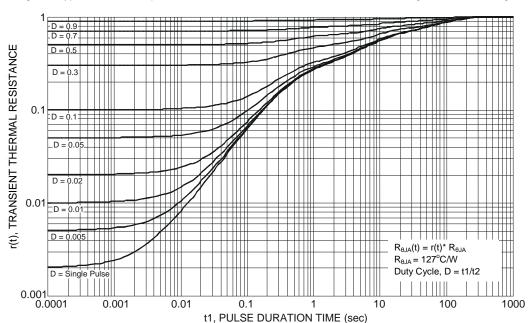
Figure 7 Gate Threshold Variation vs. Junction Temperature



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10 V<sub>GS</sub> GATE THRESHOLD VOLTAGE (V)  $V_{DS} = 15V$ 8 6 2 0 16 0 2 10 12 Q<sub>g</sub>, TOTAL GATE CHARGE (nC) Figure 10 Gate Charge

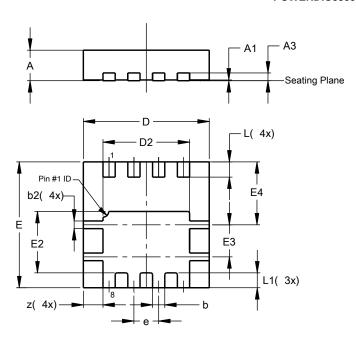




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### POWERDI®3333-8

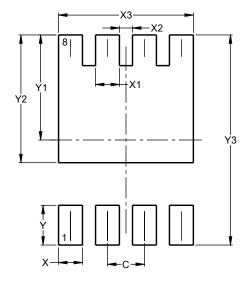


POWERDI®3333-8						
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
<b>A</b> 1	0.00	0.05	0.02			
A3	_	_	0.203			
b	0.27	0.37	0.32			
b2	0.15	0.25	0.20			
D	3.25	3.35	3.30			
D2	2.22	2.32	2.27			
Е	3.25	3.35	3.30			
E2	1.56	1.66	1.61			
E3	0.79	0.89	0.84			
E4	1.60	1.70	1.65			
е	-	_	0.65			
L	0.35	0.45	0.40			
L1	_	_	0.39			
Z	-	_	0.515			
All Dimensions in mm						

## **Suggested Pad Layout**

 $\label{prop:lease} Please see \ http://www.diodes.com/package-outlines.html for the latest version.$ 

#### POWERDI®3333-8



Dimensions	Value (in mm)
С	0.650
Х	0.420
X1	0.420
X2	0.230
Х3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700



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